CSD95377Q4M Synchronous Buck NexFET™ Power Stage

1 Features

- Above 94% System Efficiency at 15 A
- Max Rated Continuous Current 35 A
- High-Frequency Operation (up to 2 MHz)
- High-Density SON 3.5-mm × 4.5-mm Footprint
- Ultra-Low Inductance Package
- System-Optimized PCB Footprint
- 3.3-V and 5-V PWM Signal Compatible
- Diode Emulation Mode With Forced Continuous Conduction Mode (FCCM)
- Input Voltages to 16 V
- Tri-State PWM Input
- Integrated Bootstrap Diode
- Shoot-Through Protection
- RoHS Compliant – Lead Free Terminal Plating
- Halogen Free

2 Applications

- Point-of-Load Synchronous Buck in Server, Networking, Telecom Systems
- Multiphase Vcore, DDR, and Graphics Solutions

3 Description

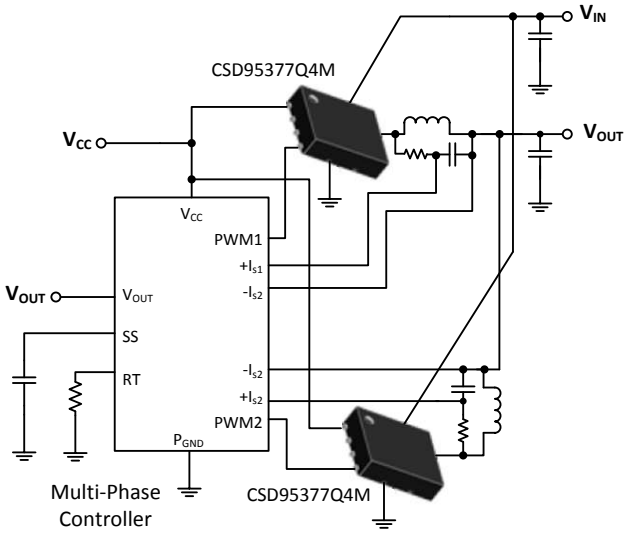
The CSD95377Q4M NexFET™ power stage is a highly-optimized design for use in a high power, high density synchronous buck converter. This product integrates the driver IC and power MOSFETs to complete the power stage switching function. The driver IC has built-in selectable diode emulation function enables Discontinuous Conduction Mode (DCM) operation to improve light load efficiency. This combination produces high-current, high-efficiency, and high-speed switching capability in a small 3.5 mm × 4.5 mm outline package. In addition, the PCB footprint has been optimized to help reduce design time and simplify the completion of the overall system design.

Device Information(1)

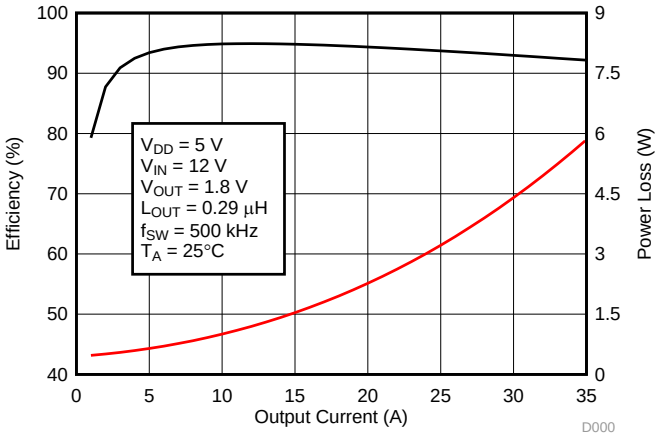
DEVICE	MEDIA	QTY	PACKAGE	SHIP
CSD95377Q4M	13-Inch Reel	2500	SON 3.50-mm × 4.50-mm Plastic Package	Tape and Reel
CSD95377Q4MT	7-Inch Reel	250		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Application Diagram



Typical Power Stage Efficiency and Power Loss



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4 Revision History

Changes from Revision A (January 2017) to Revision B **Page**

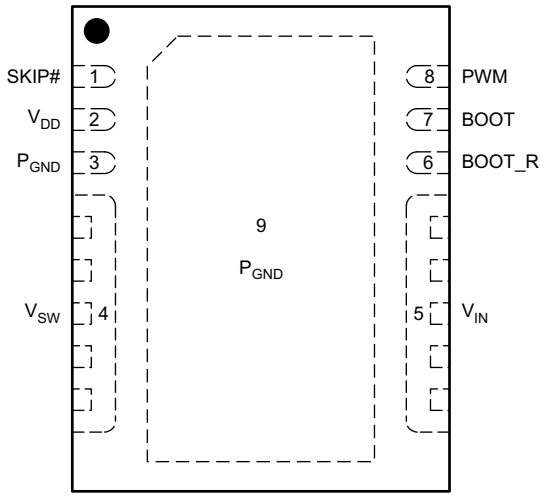
- Changed *Feature* From: "Max Rated Continuous Current 30 A" To: "Max Rated Continuous Current 35 A" ... 1
- Updated the *Typical Power Stage Efficiency and Power Loss* figure to reflect 35 A maximum current. ... 1
- Changed the I_{OUT} Continuous output current MAX value From: 30 A To: 35 A in the *Recommended Operating Conditions* table. ... 4
- Updated Figure 4, Figure 5, Figure 6, Figure 7, Figure 8, Figure 9, Figure 10, Figure 11, and Figure 15 to reflect 35 A maximum current. ... 10
- Changed the calculating values in the *Design Example* to reflect 35 A maximum current. ... 13

Changes from Original (December 2015) to Revision A **Page**

- Changed unit for Hysteresis parameter from mV : to V in the *Electrical Characteristics* table ... 5
- Added *Receiving Notification of Documentation Updates* section to *Device and Documentation Support* section ... 15

5 Pin Configuration and Functions

SON 3.5 × 4.5 mm
Top View



Pin Functions

PIN		DESCRIPTION
NO.	NAME	
1	SKIP#	This pin enables the diode emulation function. When this pin is held low, Diode Emulation Mode is enabled for the sync FET. When SKIP# is high, the CSD95377Q4M operates in Forced Continuous Conduction Mode. A tri-state voltage on SKIP# puts the driver into a very-low power state.
2	V_{DD}	Supply voltage to gate drivers and internal circuitry.
3	P_{GND}	Power ground, needs to be connected to pin 9 and PCB.
4	V_{SW}	Voltage switching node – pin connection to the output inductor.
5	V_{IN}	Input voltage pin. Connect input capacitors close to this pin.
6	BOOT_R	Bootstrap capacitor connection. Connect a minimum 0.1-µF, 16-V, X5R ceramic capacitor from BOOT to BOOT_R pins. The bootstrap capacitor provides the charge to turn on the control FET. The bootstrap diode is integrated. Boot_R is internally connected to V_{SW}.
7	BOOT	
8	PWM	Pulse width modulated tri-state input from external controller. Logic low sets control FET gate low and sync FET gate high. Logic high sets control FET gate high and sync FET gate low. Open or Hi-Z sets both MOSFET gates low if greater than the tri-state shutdown hold-off time (t_{3HT}).
9	P_{GND}	Power ground.

6 Specifications

6.1 Absolute Maximum Ratings

T_A = 25°C (unless otherwise noted)(1)

		MIN	MAX	UNIT
	V_{IN} to P_{GND}	–0.3	20	V
	V_{SW} to P_{GND} , V_{IN} to V_{SW}	–0.3	20	V
	V_{SW} to P_{GND}, V_{IN} to V_{SW} (<10 ns)	–7	23	V
	V_{DD} to P_{GND}	–0.3	6	V
	PWM, SKIP# to P_{GND}	–0.3	6	V
	BOOT to P_{GND}	–0.3	25	V
	BOOT to P_{GND} (<10 ns)	–2	28	V
	BOOT to BOOT_R	–0.3	6	V
	BOOT to BOOT_R (duty cycle < 0.2%)		8	V
P_D	Power dissipation		8	W
T_J	Operating temperature	–40	150	°C
T_{stg}	Storage temperature	–55	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM)(1)	±1000	V
		Charged-device model (CDM)(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

T_A = 25°C (unless otherwise noted)

			MIN	MAX	UNIT
V_{DD}	Gate drive voltage		4.5	5.5	V
V_{IN}	Input supply voltage (1)			16	V
I_{OUT}	Continuous output current	V_{IN} = 12 V, V_{DD} = 5 V, V_{OUT} = 1.8 V, f_{SW} = 500 kHz, L_{OUT} = 0.29 µH(2)		35	A
I_{OUT-PK}	Peak output current(2)(3)			70	A
f_{SW}	Switching frequency	C_{BST} = 0.1 µF (min)		2000	kHz
	On-time duty cycle			85%	
	Minimum PWM On-time		40		ns
	Operating temperature		–40	125	°C

(1) Operating at high V_{IN} can create excessive AC voltage overshoots on the switch node (V_{SW}) during MOSFET switching transients. For reliable operation, the switch node (V_{SW}) to ground voltage must remain at or below the *Absolute Maximum Ratings*.
(2) Peak output current is applied for t_p = 10 ms, duty cycle ≤ 1%.
(3) Measurement made with six 10-µF (TDK C3216X5R1C106KT or equivalent) ceramic capacitors placed across V_{IN} to P_{GND} pins.

6.4 Thermal Information

T_A = 25°C (unless otherwise noted)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC(top)}$	Thermal resistance junction-to-case (top of package)(1)			22.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance(2)			2.5	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-in^2 (6.45-cm^2), 2-oz (0.071-mm) thick Cu pad on a 1.5-in × 1.5-in, 0.06-in (1.52-mm) thick FR4 board.
(2) $R_{\theta JB}$ value based on hottest board temperature within 1 mm of the package.

6.5 Electrical Characteristics

T_A = 25°C, V_{DD} = POR to 5.5 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{LOSS}						
	Power loss(1)	V_{IN} = 12 V, V_{DD} = 5 V, V_{OUT} = 1.8 V, I_{OUT} = 15 A, f_{SW} = 500 kHz, L_{OUT} = 0.29 µH, T_J = 25°C		1.6		W
	Power loss(1)	V_{IN} = 12 V, V_{DD} = 5 V, V_{OUT} = 1.8 V, I_{OUT} = 15 A, f_{SW} = 500 kHz, L_{OUT} = 0.29 µH, T_J = 125°C		1.8		W
V_{IN}						
I_Q	V_{IN} quiescent current	PWM = float			1	µA
V_{DD}						
I_{DD}	Standby supply current	PWM = float, $V_{SKIP\#}$ = V_{DD} or 0 V		130		µA
		$V_{SKIP\#}$ = float		8		
I_{DD}	Operating supply current	PWM = 50% duty cycle, f_{SW} = 500 kHz		8.6		mA
POWER-ON RESET AND UNDERVOLTAGE LOCKOUT						
V_{DD} rising	Power-on reset				4.15	V
V_{DD} falling	UVLO		3.7			V
	Hysteresis			0.2		V
PWM AND SKIP# I/O SPECIFICATIONS						
R_I	Input impedance	Pullup to V_{DD}		1700		kΩ
		Pulldown (to GND)		800		kΩ
V_{IH}	Logic level high		2.65			V
V_{IL}	Logic level low				0.6	V
V_{IHH}	Hysteresis			0.2		V
V_{TS}	Tri-state voltage		1.3		2	V
$t_{THOLD(off1)}$	Tri-state activation time (falling) PWM			60		ns
$t_{THOLD(off2)}$	Tri-state activation time (rising) PWM			60		ns
t_{TSKF}	Tri-state activation time (falling) SKIP#			1		ns
t_{TSKR}	Tri-state activation time (rising) SKIP#			1		µs
$t_{3RD(PWM)}$	Tri-state exit time PWM(2)				100	ns
$t_{3RD(SKIP\#)}$	Tri-state exit time SKIP#(2)				50	µs
BOOTSTRAP SWITCH						
V_{FBST}	Forward voltage	I_F = 10 mA		120	240	mV
I_{RLEAK}	Reverse leakage(2)	V_{BOOT} – V_{DD} = 25 V			2	µA

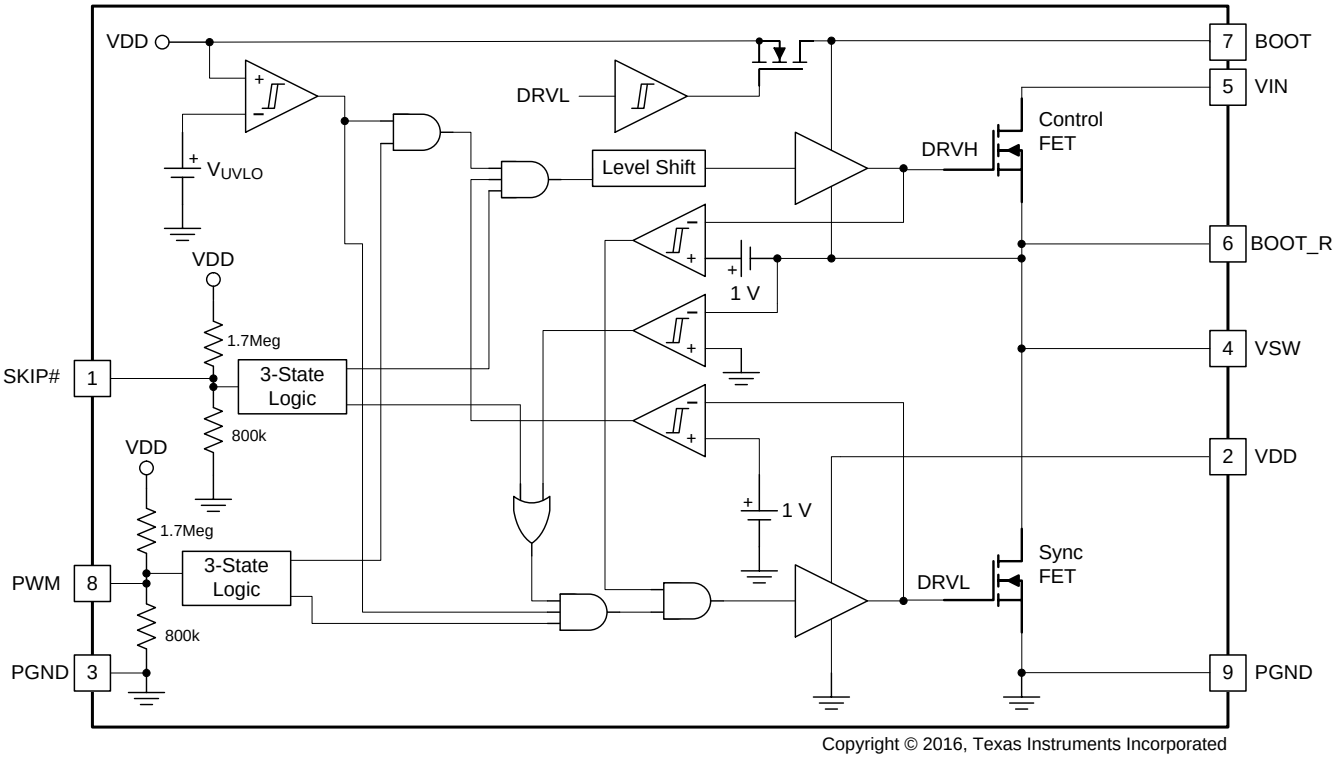
(1) Measurement made with six 10-µF (TDK C3216X5R1C106KT or equivalent) ceramic capacitors placed across V_{IN} to P_{GND} pins.
(2) Specified by design.

7 Detailed Description

7.1 Overview

The CSD95377Q4M™ power stage is a highly-optimized design for use in a high-power, high-density synchronous buck converter.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Powering CSD95377Q4M and Gate Drivers

An external V_{DD} voltage is required to supply the integrated gate driver IC and provide the necessary gate drive power for the MOSFETs. TI recommends a 1-µF, 10-V, X5R or higher ceramic capacitor to bypass V_{DD} pin to P_{GND}. A bootstrap circuit to provide gate drive power for the control FET is also included. The bootstrap supply to drive the control FET is generated by connecting a 100-nF, 16-V, X5R ceramic capacitor between BOOT and BOOT_R pins. An optional R_{BOOT} resistor can be used to slow down the turnon speed of the control FET and reduce voltage spikes on the V_{SW} node. A typical 1-Ω to 4.7-Ω value is a compromise between switching loss and V_{SW} spike amplitude.

7.3.2 Undervoltage Lockout (UVLO) Protection

The UVLO comparator evaluates the VDD voltage level. As V_{VDD} rises, both the control FET and sync FET gates hold actively low at all times until V_{VDD} reaches the higher UVLO threshold (V_{UVLO_H}). Then the driver becomes operational and responds to PWM and SKIP# commands. If VDD falls below the lower UVLO threshold (V_{UVLO_L} = V_{UVLO_H} – hysteresis), the device disables the driver and drives the outputs of the control FET and Sync FET gates actively low. Figure 1 shows this function.

CAUTION

Do not start the driver in the very-low power mode (SKIP# = Tri-state).

Feature Description (continued)

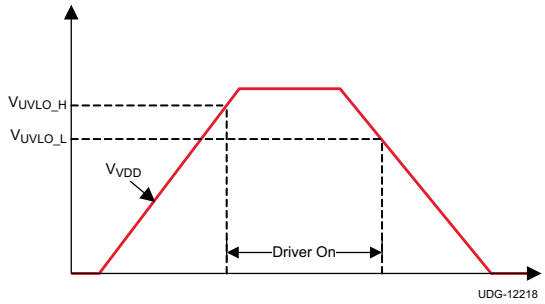


Figure 1. UVLO Operation

7.3.3 PWM Pin

The PWM pin incorporates an input tri-state function. The device forces the gate driver outputs to low when PWM is driven into the tri-state window and the driver enters a low-power state with zero exit latency. The pin incorporates a weak pullup to maintain the voltage within the tri-state window during low-power modes. Operation into and out of tri-state mode follows the timing diagram outlined in Figure 2.

When VDD reaches the UVLO_H level, a tri-state voltage range (window) is set for the PWM input voltage. The window is defined as the PWM voltage range between PWM logic high (V_{IH}) and logic low (V_{IL}) thresholds. The device sets high-level input voltage and low-level input voltage threshold levels to accommodate both 3.3-V (typical) and 5-V (typical) PWM drive signals.

When the PWM exits tri-state, the driver enters CCM for a period of 4 µs, regardless of the state of the SKIP# pin. Normal operation requires this time period for the auto-zero comparator to resume.

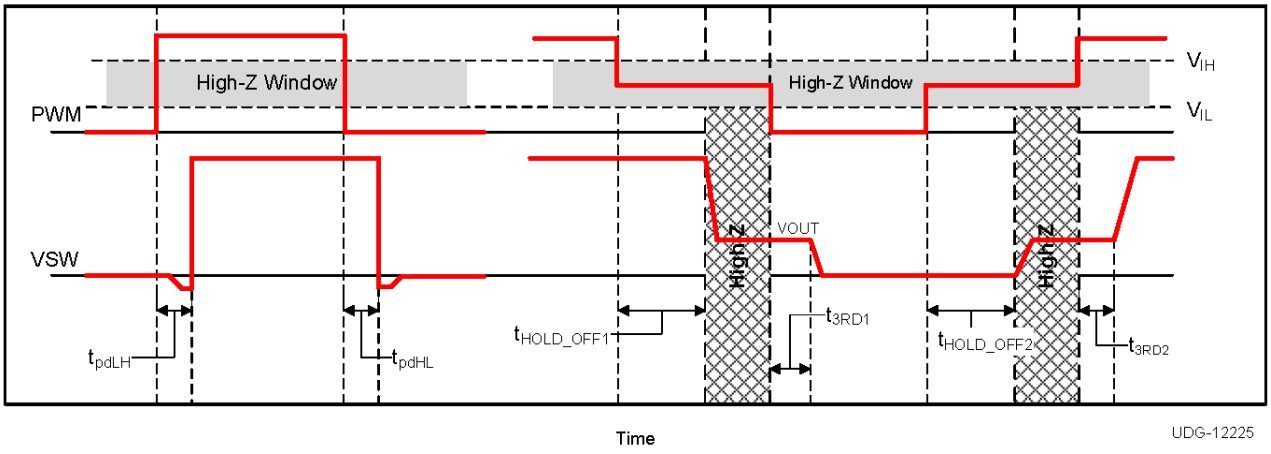


Figure 2. PWM Tri-State Timing Diagram

7.3.4 SKIP# Pin

The SKIP# pin incorporates the input tri-state buffer as PWM. The function is somewhat different. When SKIP# is low, the zero crossing (ZX) detection comparator is enabled, and DCM operation occurs if the load current is less than the critical current. When SKIP# is high, the ZX comparator disables, and the converter enters FCCM mode. When both SKIP# and PWM are tri-stated, normal operation forces the gate driver outputs low and the driver enters a low-power state. In the low-power state, the UVLO comparator remains off to reduce quiescent current. When SKIP# is pulled low, the driver wakes up and is able to accept PWM pulses in less than 50 µs.

Feature Description (continued)

Table 1 shows the logic functions of UVLO, PWM, SKIP#, the control FET gate, and the sync FET gate.

Table 1. Logic Functions of the Driver IC

UVLO	PWM	SKIP#	SYNC FET GATE	CONTROL FET GATE	MODE
Active	—	—	Low	Low	Disabled
Inactive	Low	Low	High(1)	Low	DCM(1)
Inactive	Low	High	High	Low	FCCM
Inactive	High	H or L	Low	High	
Inactive	Tri-state	H or L	Low	Low	LQ(2)
Inactive	—	Tri-state	Low	Low	ULQ(3)

(1) Until zero crossing protection occurs.
(2) Low-quiescent current (LQ).
(3) Ultra-low quiescent current (ULQ).

7.3.4.1 Zero Crossing (ZX) Operation

The zero crossing comparator is adaptive for improved accuracy. As the output current decreases from a heavy load condition, the inductor current also reduces and eventually arrives at a *valley*, where it touches zero current, which is the boundary between continuous conduction and discontinuous conduction modes. The SW pin detects the zero-current condition. When this zero inductor current condition occurs, the ZX comparator turns off the rectifying MOSFET.

7.3.5 Integrated Boost-Switch

To maintain a BST-SW voltage close to VDD (to get lower conduction losses on the high-side FET), the conventional diode between the VDD pin and the BST pin is replaced by a FET which is gated by the DRVL signal.

7.4 Device Functional Modes

Table 1 shows the different functional modes of CSD95377. The diode emulation mode is enabled with SKIP# pulled low, which improves light load efficiency. With PWM in tri-state, the power stage enters LQ mode and the quiescent current is reduced to 130 µA. When SKIP# is held in tri-state, ULQ mode is enabled and the current is decreased to 8 µA.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The power stage CSD95377Q4M is a highly-optimized design for synchronous buck applications using NexFET devices with a 5-V gate drive. The control FET and sync FET silicon are parametrically tuned to yield the lowest power loss and highest system efficiency. As a result, a rating method is used that is tailored toward a more systems-centric environment. The high-performance gate driver IC integrated in the package helps minimize the parasitics and results in extremely fast switching of the power MOSFETs. System-level performance curves such as power loss, SOA, and normalized graphs allow engineers to predict the product performance in the actual application.

8.2 Typical Application

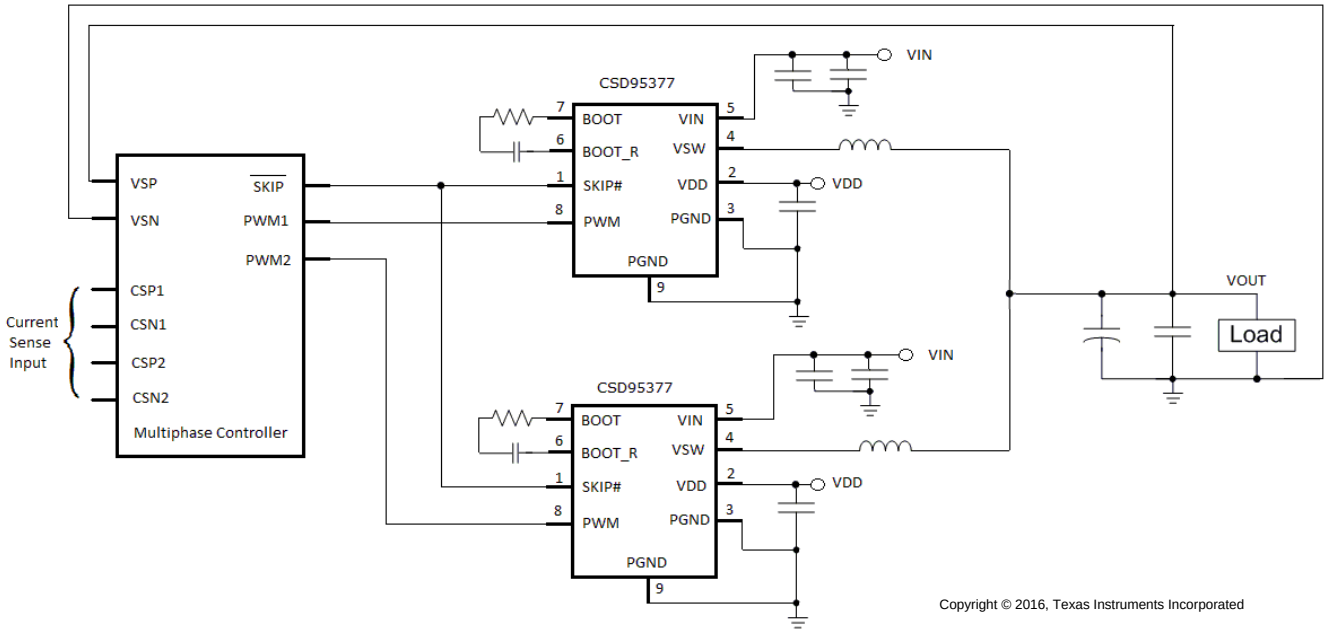
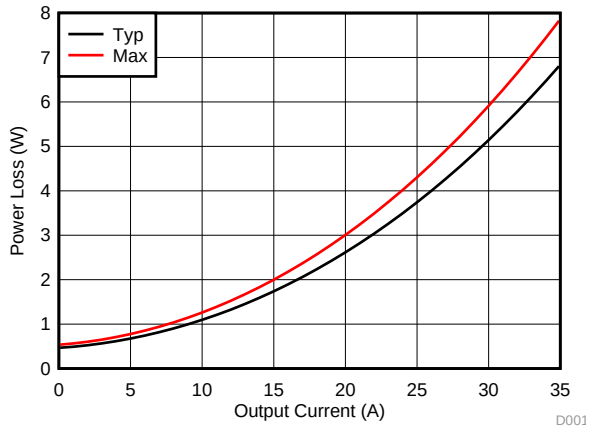


Figure 3. Application Schematic

Typical Application (continued)

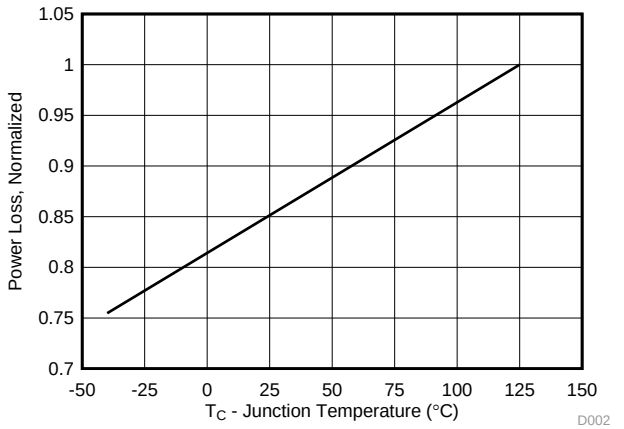
8.2.1 Application Curves

T_J = 125°C, unless stated otherwise.



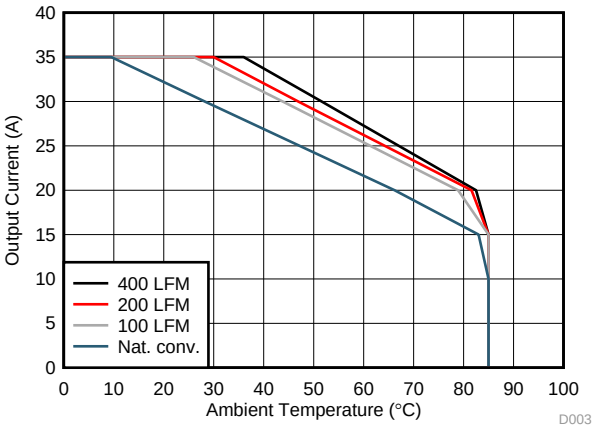
V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 4. Power Loss vs Output Current



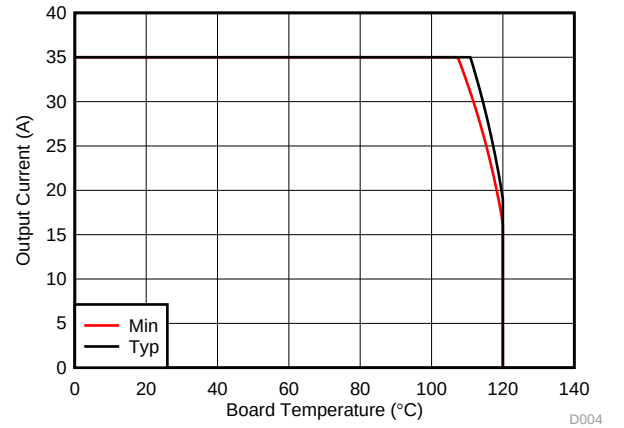
V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 5. Power Loss vs Temperature



V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 6. Safe Operating Area – PCB Horizontal Mount (1)



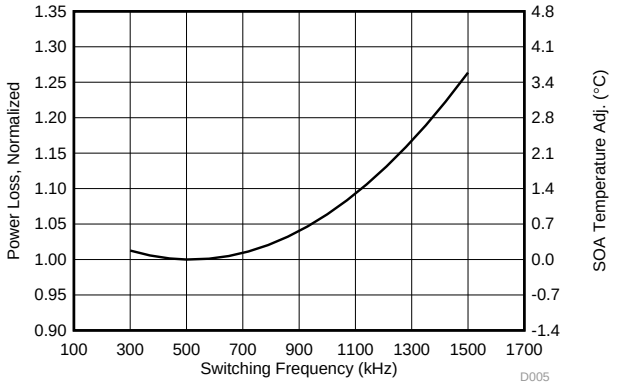
V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 7. Typical Safe Operating Area (1)

1. The typical CSD95377Q4M system characteristic curves are based on measurements made on a PCB design with dimensions of 4 in (W) × 3.5 in (L) × 0.062 in (T) and 6 copper layers of 1-oz copper thickness. See *System Example* for detailed explanation.

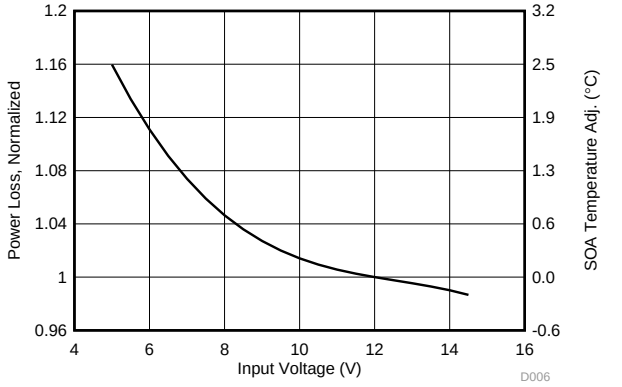
Typical Application (continued)

T_J = 125°C, unless stated otherwise.



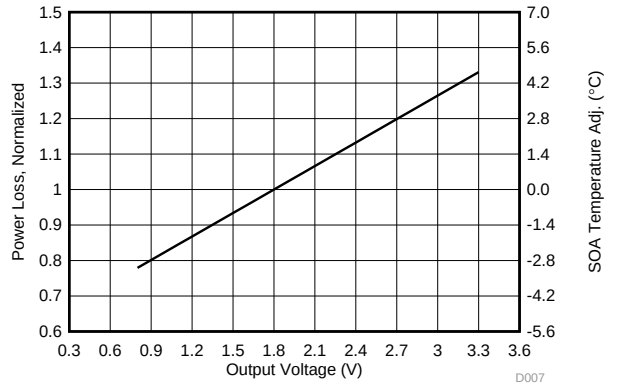
V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
I_{OUT} = 35 A L_{OUT} = 0.29 µH

Figure 8. Normalized Power Loss vs Frequency



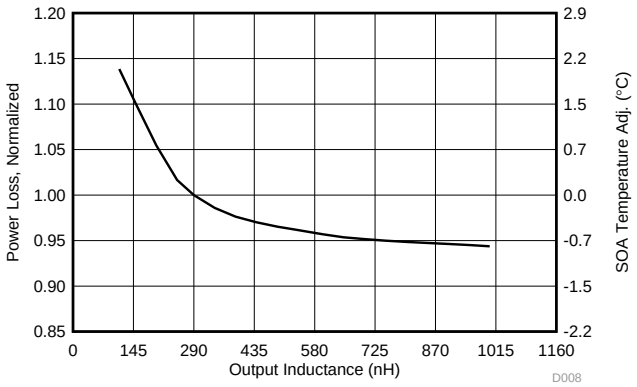
I_{OUT} = 35 A V_{DD} = 5 V V_{OUT} = 1.8 V
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 9. Normalized Power Loss vs Input Voltage



V_{IN} = 12 V V_{DD} = 5 V I_{OUT} = 35 A
f_{SW} = 500 kHz L_{OUT} = 0.29 µH

Figure 10. Normalized Power Loss vs Output Voltage

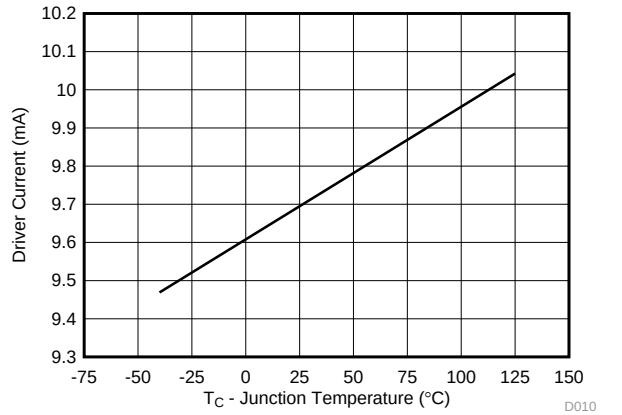


V_{IN} = 12 V V_{DD} = 5 V I_{OUT} = 35 A
f_{SW} = 500 kHz V_{OUT} = 1.8 V

Figure 11. Normalized Power Loss vs Output Inductance

V_{IN} = 12 V V_{DD} = 5 V I_{OUT} = 35 A
L_{OUT} = 0.29 µH V_{OUT} = 1.8 V

Figure 12. Driver Current vs Frequency



V_{IN} = 12 V V_{DD} = 5 V V_{OUT} = 1.8 V
I_{OUT} = 35 A L_{OUT} = 0.29 µH

Figure 13. Driver Current vs Temperature

8.3 System Example

8.3.1 Power Loss Curves

MOSFET-centric parameters such as $R_{DS(ON)}$ and Q_{gd} are primarily needed by engineers to estimate the loss generated by the devices. In an effort to simplify the design process for engineers, Texas Instruments has provided measured power loss performance curves. Figure 4 plots the power loss of the CSD95377Q4M as a function of load current. This curve is measured by configuring and running the CSD95377Q4M as it would be in the final application (see Figure 14). The measured power loss is the CSD95377Q4M device power loss which consists of both input conversion loss and gate drive loss. Equation 1 is used to generate the power loss curve.

$$\textbf{Power loss} = (V_{IN} \times I_{IN}) + (V_{DD} \times I_{DD}) - (V_{SW\_AVG} \times I_{OUT}) \quad (1)$$

The power loss curve in Figure 4 is measured at the maximum recommended junction temperature of T_J = 125°C under isothermal test conditions.

8.3.2 Safe Operating Area (SOA) Curves

The SOA curves in the CSD95377Q4M data sheet give engineers guidance on the temperature boundaries within an operating system by incorporating the thermal resistance and system power loss. Figure 6 and Figure 7 outline the temperature and airflow conditions required for a given load current. The area under the curve dictates the safe operating area. All the curves are based on measurements made on a PCB design with dimensions of 4 in (W) × 3.5 in (L) × 0.062 in (T) and 6 copper layers of 1-oz copper thickness.

8.3.3 Normalized Curves

The normalized curves in the CSD95377Q4M data sheet give engineers guidance on the power loss and SOA adjustments based on their application specific needs. These curves show how the power loss and SOA boundaries will adjust for a given set of systems conditions. The primary Y-axis is the normalized change in power loss and the secondary Y-axis is the change is system temperature required in order to comply with the SOA curve. The change in power loss is a multiplier for the power loss curve and the change in temperature is subtracted from the SOA curve.

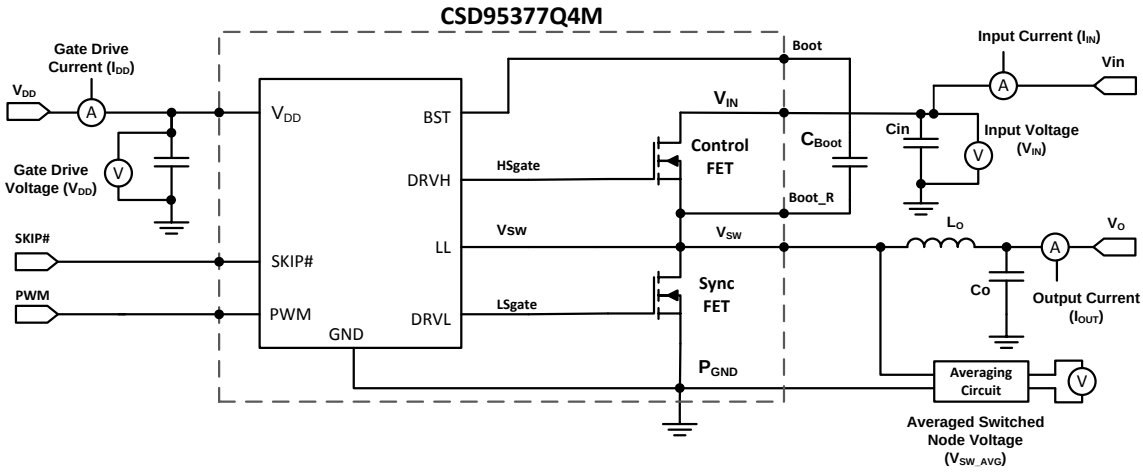


Figure 14. Power Loss Test Circuit

8.3.4 Calculating Power Loss and SOA

The user can estimate product loss and SOA boundaries by arithmetic means (see the *Design Example*). Though the power loss and SOA curves in this data sheet are taken for a specific set of test conditions, the following procedure will outline the steps engineers should take to predict product performance for any set of system conditions.

System Example (continued)

8.3.4.1 Design Example

Operating conditions: Output current (I_{OUT}) = 25 A, input voltage (V_{IN}) = 7 V, output voltage (V_{OUT}) = 2 V, switching frequency (f_{SW}) = 800 kHz, output inductor (L_{OUT}) = 0.2 µH

8.3.4.2 Calculating Power Loss

- Typical power loss at 25 A = 3.74 W (Figure 4)
- Normalized power loss for switching frequency ≈ 1.02 (Figure 8)
- Normalized power loss for input voltage ≈ 0.99 (Figure 9)
- Normalized power loss for output voltage ≈ 1.04 (Figure 10)
- Normalized power loss for output inductor ≈ 1.01 (Figure 11)
- **Final calculated Power Loss = 3.741 W × 1.02 × 0.99 × 1.04 × 1.01 ≈ 3.97 W**

8.3.4.3 Calculating SOA Adjustments

- SOA adjustment for switching frequency ≈ 0.3°C (Figure 8)
- SOA adjustment for input voltage ≈ –0.12°C (Figure 9)
- SOA adjustment for output voltage ≈ 0.62°C (Figure 10)
- SOA adjustment for output inductor ≈ 0.25°C (Figure 11)
- **Final calculated SOA adjustment = 0.3 + (–0.12) + 0.62 + 0.25 ≈ 1.05°C**

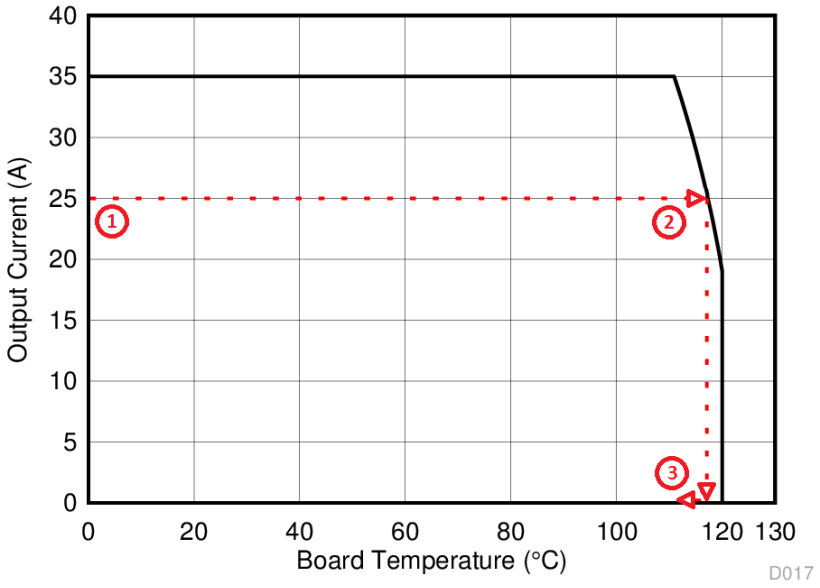


Figure 15. Power Stage CSD95377Q4M SOA

In the previous design example, the estimated power loss of the CSD95377Q4M would increase to 3.97 W. In addition, the maximum allowable board and/or ambient temperature would have to decrease by 1.05°C. Figure 15 graphically shows how the SOA curve would be adjusted accordingly.

1. Start by drawing a horizontal line from the application current to the SOA curve.
2. Draw a vertical line from the SOA curve intercept down to the board/ambient temperature.
3. Adjust the SOA board/ambient temperature by subtracting the temperature adjustment value.

In the design example, the SOA temperature adjustment yields a reduction in allowable board/ambient temperature of 1.05°C. In the event the adjustment value is a negative number, subtracting the negative number would yield an increase in allowable board and ambient temperature.

9 Layout

9.1 Layout Guidelines

9.1.1 Recommended PCB Design Overview

Two key system-level parameters can be addressed with a proper PCB design: electrical and thermal performance. Properly optimizing the PCB layout yields maximum performance in both areas. A brief description follows on how to address each parameter.

9.1.2 Electrical Performance

The CSD95377Q4M has the ability to switch at voltage rates greater than 10 kV/µs. Take special care with the PCB layout design and placement of the input capacitors, inductor, and output capacitors.

- The placement of the input capacitors relative to V_{IN} and P_{GND} pins of the CSD95377Q4M device should have the highest priority during the component placement routine. It is critical to minimize these node lengths. As such, ceramic input capacitors need to be placed as close as possible to the V_{IN} and P_{GND} pins (see Figure 16). The example in Figure 16 uses 1 × 1-nF 0402, 25-V and 3 × 10-µF 1206, 25-V ceramic capacitors (TDK part number C3216X5R1C106KT or equivalent). Notice there are ceramic capacitors on both sides of the board with an appropriate amount of vias interconnecting both layers. In terms of priority of placement next to the power stage C5, C8, C6, and C19 should follow in order.
- The bootstrap capacitor C_{BOOT} 0.1-µF 0603, 16-V ceramic capacitor should be closely connected between BOOT and BOOT_R pins.
- The switching node of the output inductor should be placed relatively close to the power stage CSD95377Q4M V_{SW} pins. Minimizing the V_{SW} node length between these two components will reduce the PCB conduction losses and actually reduce the switching noise level. (1)

9.2 Layout Example

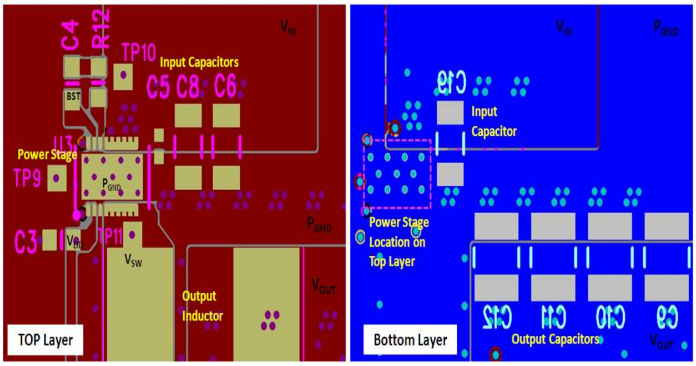


Figure 16. Recommended PCB Layout (Top-Down View)

9.3 Thermal Considerations

The CSD95377Q4M has the ability to use the P_{GND} planes as the primary thermal path. As such, the use of thermal vias is an effective way to pull away heat from the device and into the system board. Concerns of solder voids and manufacturability problems can be addressed by the use of three basic tactics to minimize the amount of solder attach that will wick down the via barrel:

- Intentionally space out the vias from each other to avoid a cluster of holes in a given area.
- Use the smallest drill size allowed in your design. The example in Figure 16 uses vias with a 10-mil drill hole and a 16-mil capture pad.
- Tent the opposite side of the via with solder-mask.

The number and drill size of the thermal vias should align with the end user's PCB design rules and manufacturing capabilities.

(1) Keong W. Kam, David Pommerenke, "EMI Analysis Methods for Synchronous Buck Converter EMI Root Cause Analysis", University of Missouri – Rolla

10 Device and Documentation Support

10.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

10.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

10.3 Trademarks

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10.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

10.5 Glossary

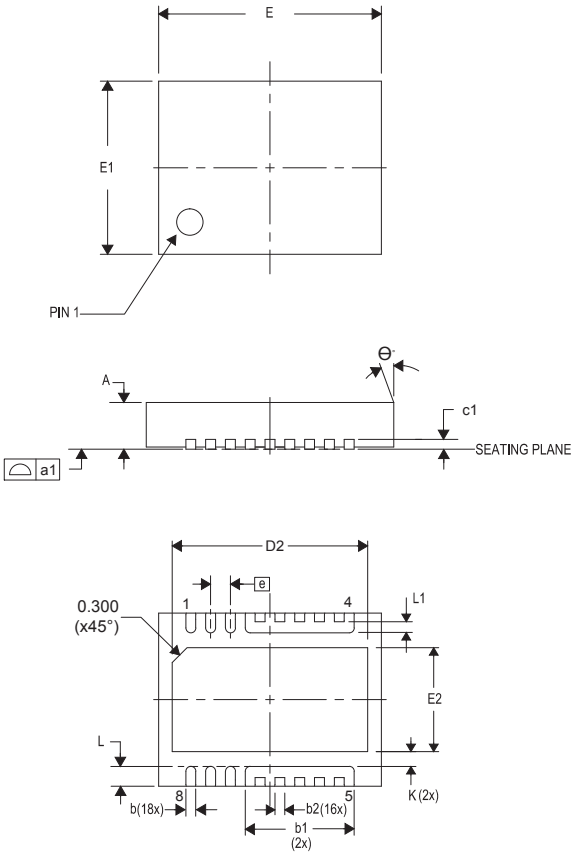
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

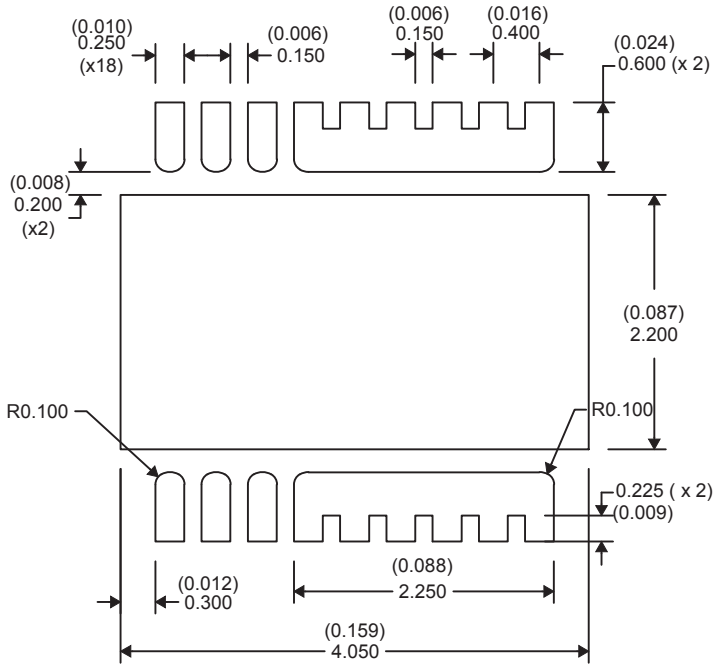
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

11.1 Mechanical Drawing

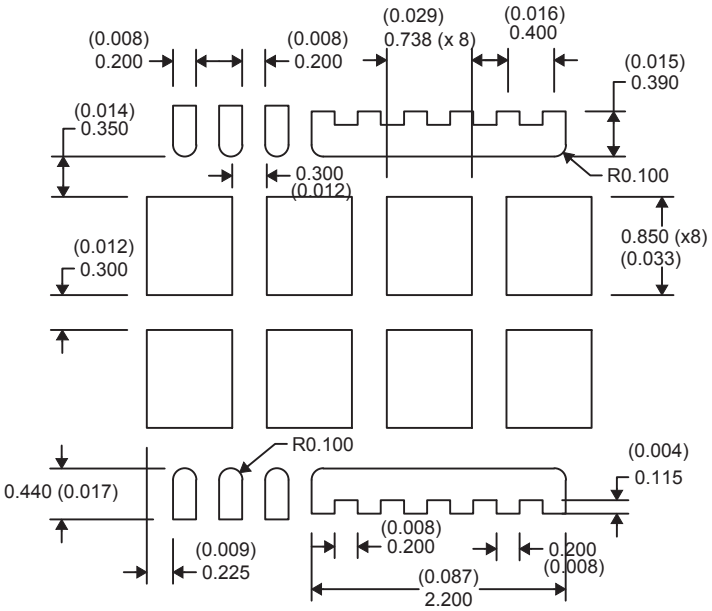


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.800	0.900	1.000	0.031	0.035	0.039
a1	0.000	0.000	0.080	0.000	0.000	0.003
b	0.150	0.200	0.250	0.006	0.008	0.010
b1	2.000	2.200	2.400	0.079	0.087	0.095
b2	0.150	0.200	0.250	0.006	0.008	0.010
c1	0.150	0.200	0.250	0.006	0.008	0.010
D2	3.850	3.950	4.050	0.152	0.156	0.160
E	4.400	4.500	4.600	0.173	0.177	0.181
E1	3.400	3.500	3.600	0.134	0.138	0.142
E2	2.000	2.100	2.200	0.079	0.083	0.087
e	0.400 TYP			0.016 TYP		
K	0.300 TYP			0.012 TYP		
L	0.300	0.400	0.500	0.012	0.016	0.020
L1	0.180	0.230	0.280	0.007	0.009	0.011
θ	0.00	—	—	0.00	—	—

11.2 Recommended PCB Land Pattern



11.3 Recommended Stencil Opening



NOTE: Dimensions are in mm (in).
Stencil is 100-µm thick.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD95377Q4M	ACTIVE	VSON-CLIP	DPC	8	2500	RoHS-Exempt & Green	NIPDAU | SN	Level-2-260C-1 YEAR	-40 to 150	95377M	Samples
CSD95377Q4MT	ACTIVE	VSON-CLIP	DPC	8	250	RoHS-Exempt & Green	NIPDAU | SN	Level-2-260C-1 YEAR	-40 to 150	95377M	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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